



TM007EP02I5

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

$V_{DS} = -20V$ $I_D = -0.7A$

$R_{DS(ON)} = 520m\Omega (typ.) @ V_{GS} = -4.5V$

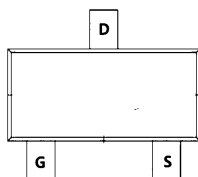
ESD protection

100% UIS Tested

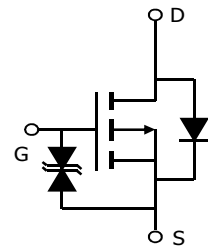
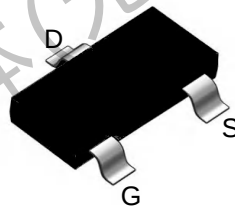
100% R_g Tested



I5:SOT-523



Marking: 39



Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-0.7	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-0.42	A
I_{DM}	Pulsed Drain Current ²	-1.75	A
P_D	Total Power Dissipation ³	150	mW
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	735	$^\circ C/W$
R	Thermal Resistance Junction Case ¹	---	---	$^\circ C/W$

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 20	μA
Gate threshold voltage (note 2)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.65	-1.0	V
Drain-source on-resistance (note 2)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1A$		520		m Ω
		$V_{GS} = -2.5V, I_D = -0.8A$		700		m Ω
		$V_{GS} = -1.8V, I_D = -0.5A$		950		m Ω
Forward transconductance (note 2)	g_{FS}	$V_{DS} = -10V, I_D = -0.54A$		1.2		S
Diode forward voltage	V_{SD}	$I_S = -0.5A, V_{GS} = 0V$			-1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113	170	pF
Output capacitance	C_{oss}			15	25	pF
Reverse transfer capacitance	C_{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	$t_{d(on)}$	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_D = -200mA, R_{GEN} = 10\Omega$		9		ns
Turn-on rise time (note 3)	t_r			5.8		ns
Turn-off delay time (note 3)	$t_{d(off)}$			32.7		ns
Turn-off fall time (note 3)	t_f			20.3		ns

Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producting.

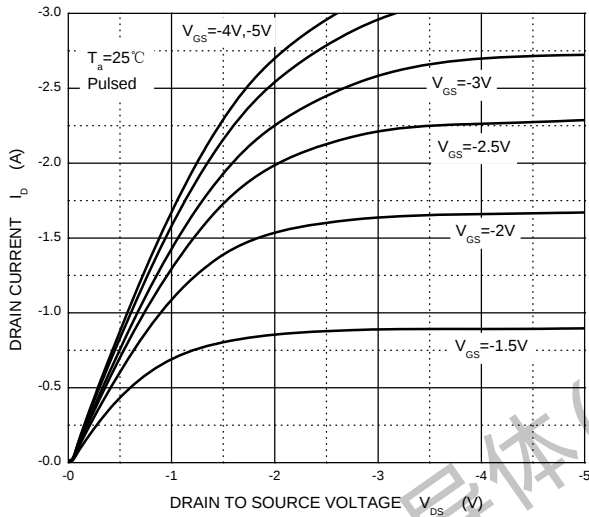


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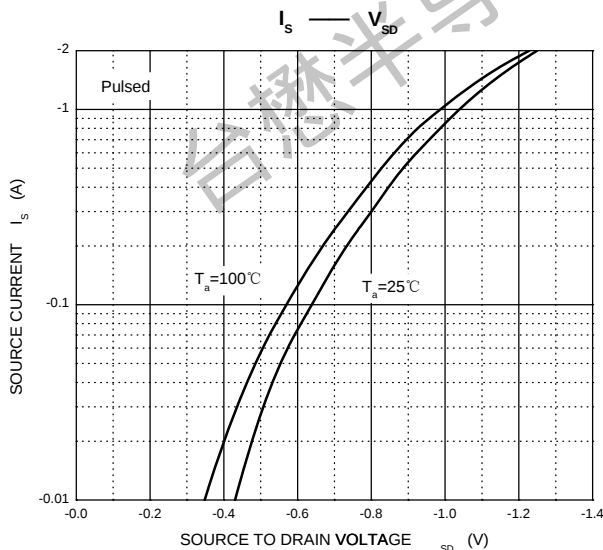
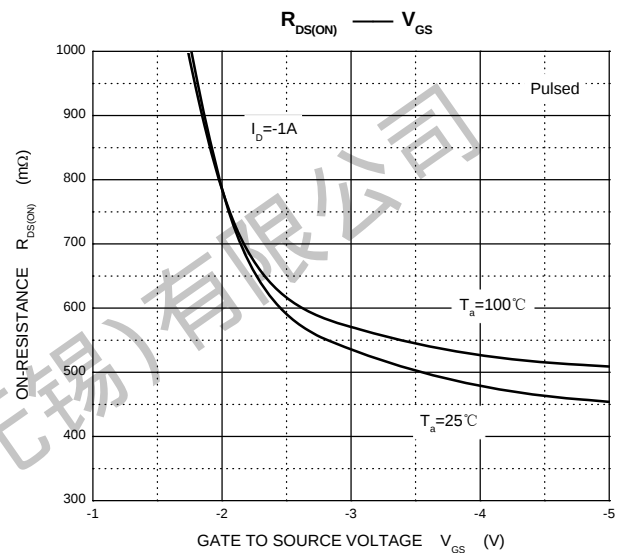
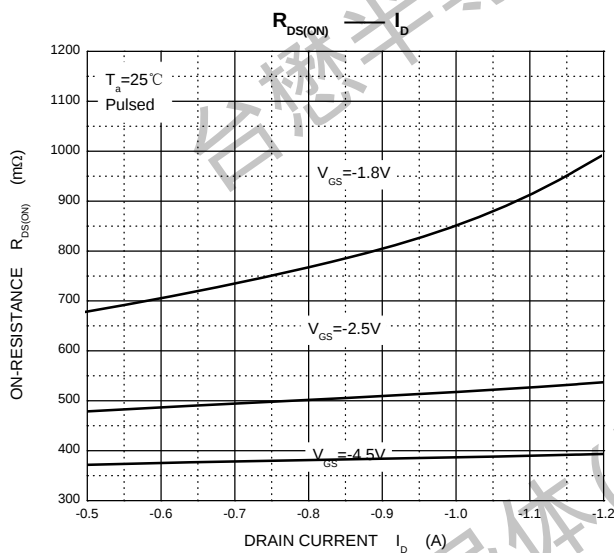
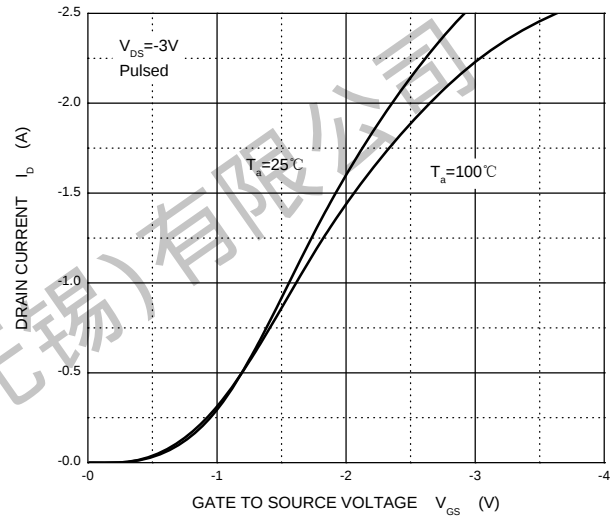
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Typical Characteristics

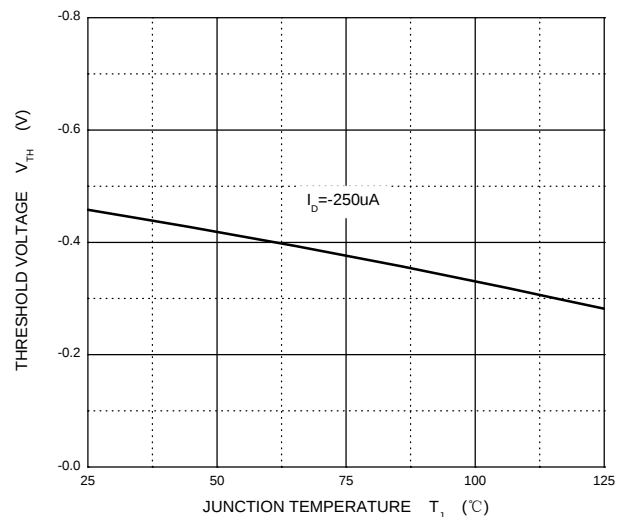
Output Characteristics



Transfer Characteristics



Threshold Voltage

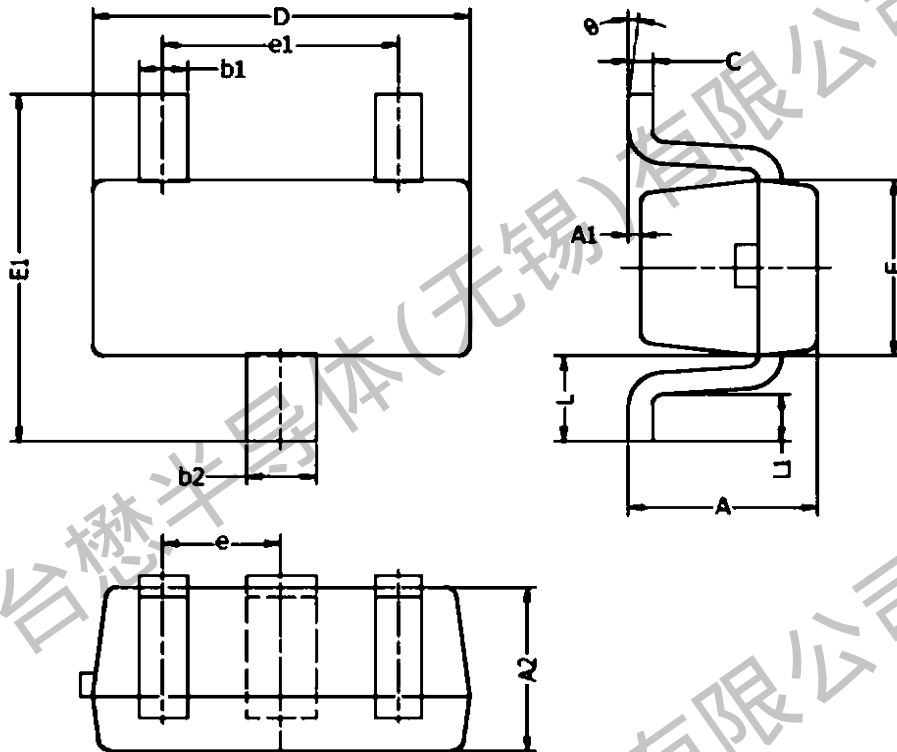




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Package Mechanical Data:SOT-523



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:

1. Above package outline conforms to JEITA EAJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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Revision history:

Date	Rev	Description	Page
2023.05.10	23.05	Original	